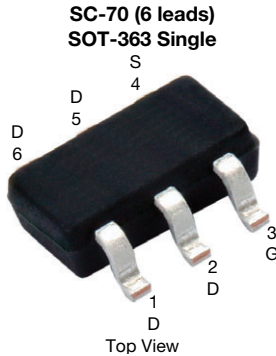


N-Channel 30 V (D-S) MOSFET



Marking code: AR

PRODUCT SUMMARY	
V_{DS} (V)	30
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 10$ V	0.058
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 4.5$ V	0.064
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 2.5$ V	0.077
Q_g typ. (nC)	3.5
I_D (A) ^a	3.9
Configuration	Single

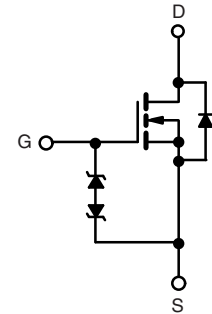
FEATURES

- TrenchFET® power MOSFET
- Typical ESD protection 1500 V in HBM
- 100 % R_g tested
- Material categorization:
for definitions of compliance please see
www.vishay.com/doc?99912


RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Portable devices such as smart phones and tablet PCs
 - DC/DC converters
 - High frequency switching
 - OVP switch
 - Load switch



N-Channel MOSFET

ORDERING INFORMATION	
Package	SC-70
Lead (Pb)-free and halogen-free	Si1416EDH-T1-GE3

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V_{DS}	30	V
Gate-source voltage	V_{GS}	± 12	
Continuous drain current ($T_J = 150$ °C)	$T_C = 25$ °C	3.9 ^a	A
	$T_C = 70$ °C	3.9 ^a	
	$T_A = 25$ °C	3.9 ^{a, b, c}	
	$T_A = 70$ °C	3.9 ^{a, b, c}	
Pulsed drain current ($t = 300$ μ s)	I_{DM}	15	
Continuous source-drain diode current	$T_C = 25$ °C	2.3 ^a	
	$T_A = 25$ °C	1.3 ^{b, c}	
Maximum power dissipation	$T_C = 25$ °C	2.8	W
	$T_C = 70$ °C	1.8	
	$T_A = 25$ °C	1.56 ^{b, c}	
	$T_A = 70$ °C	1 ^{b, c}	
Operating junction and storage temperature range	T_J, T_{stg}	-55 to +150	°C

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient ^{b, d}	$t \leq 5$ s	R_{thJA}	60	80	°C/W
Maximum junction-to-foot (drain)	Steady state	R_{thJF}	34	45	

Notes

- Package limited, $T_C = 25$ °C
- Surface mounted on 1" x 1" FR4 board
- $t = 5$ s
- Maximum under steady state conditions is 125 °C/W



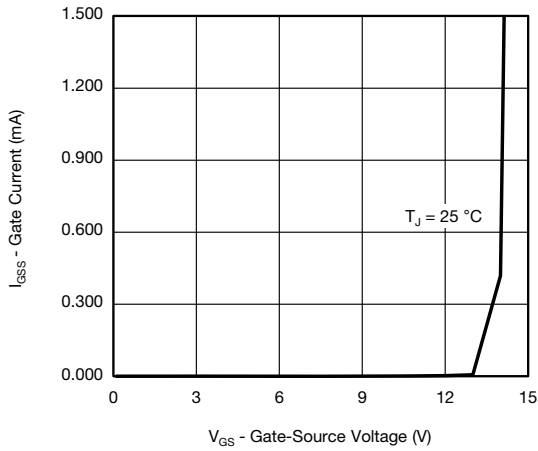
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	30	-	-	V
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$	-	34	-	mV/ $^\circ\text{C}$
$V_{GS(th)}$ temperature coefficient	$\Delta V_{GS(th)}/T_J$		-	-3.3	-	
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	0.6	-	1.4	V
Gate-source leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 4.5\text{ V}$	-	-	± 0.5	μA
		$V_{DS} = 0\text{ V}, V_{GS} = \pm 12\text{ V}$	-	-	± 20	
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$	-	-	1	
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$	-	-	10	
On-state drain current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$	10	-	-	A
Drain-source on-state resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 3.1\text{ A}$	-	0.047	0.058	Ω
		$V_{GS} = 4.5\text{ V}, I_D = 2\text{ A}$	-	0.052	0.064	
		$V_{GS} = 2.5\text{ V}, I_D = 1\text{ A}$	-	0.062	0.077	
Forward transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 3.1\text{ A}$	-	13	-	S
Dynamic ^b						
Total gate charge	Q_g	$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 4\text{ A}$	-	7.5	12	nC
		$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 4\text{ A}$	-	3.5	5.5	
Gate-source charge	Q_{gs}		-	1.8	-	
Gate-drain charge	Q_{gd}		-	0.7	-	
Gate resistance	R_g	$f = 1\text{ MHz}$	0.6	3.3	6.6	Ω
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 4.7\text{ }\Omega$ $I_D \cong 3.2\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$	-	20	40	ns
Rise time	t_r		-	60	120	
Turn-off delay time	$t_{d(off)}$		-	25	50	
Fall time	t_f		-	45	90	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 4.7\text{ }\Omega$ $I_D \cong 3.2\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$	-	1.5	5	
Rise time	t_r		-	30	60	
Turn-off delay time	$t_{d(off)}$		-	15	30	
Fall time	t_f		-	50	100	
Drain-Source Body Diode Characteristics						
Continuous source-drain diode current	I_S	$T_C = 25\text{ }^\circ\text{C}$	-	-	3.9	A
Pulse diode forward current	I_{SM}		-	-	15	
Body diode voltage	V_{SD}	$I_S = 3.2\text{ A}, V_{GS} = 0\text{ V}$	-	0.87	1.2	V
Body diode reverse recovery time	t_{rr}	$I_F = 3.2\text{ A}, di/dt = 100\text{ A}/\mu\text{s},$ $T_J = 25\text{ }^\circ\text{C}$	-	10	20	ns
Body diode reverse recovery charge	Q_{rr}		-	4	10	nC
Reverse recovery fall time	t_a		-	5.3	-	ns
Reverse recovery rise time	t_b		-	4.6	-	

Notes

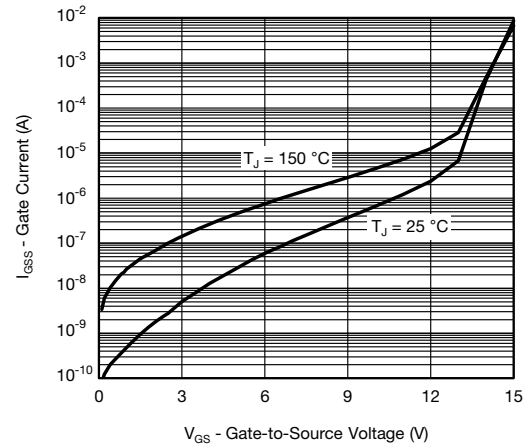
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

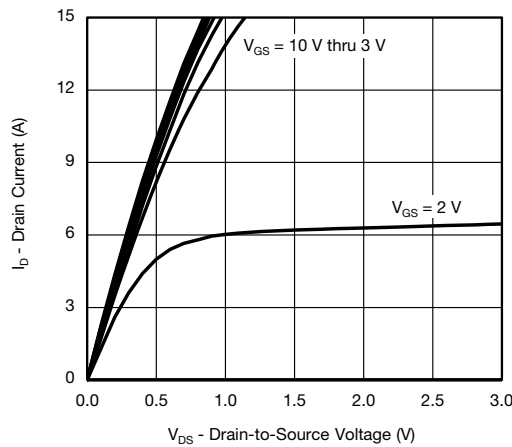
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



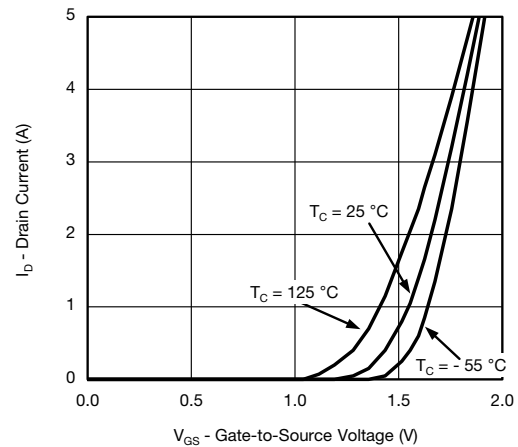
Gate Current vs. Gate-to-Source Voltage



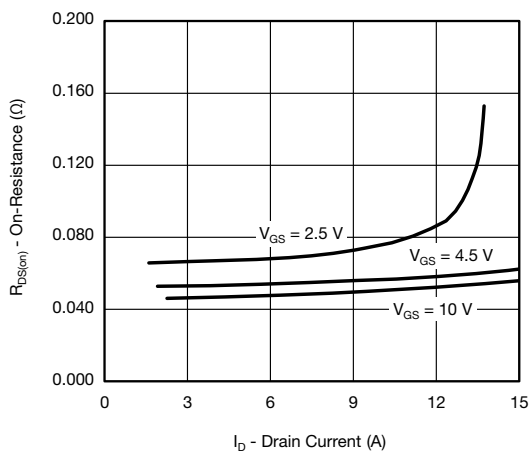
Gate Current vs. Gate-to-Source Voltage



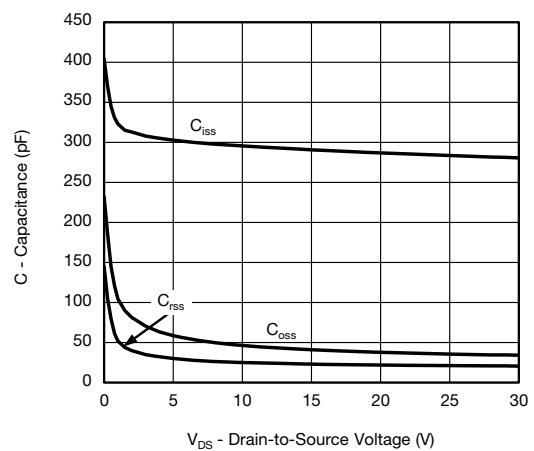
Output Characteristics



Transfer Characteristics

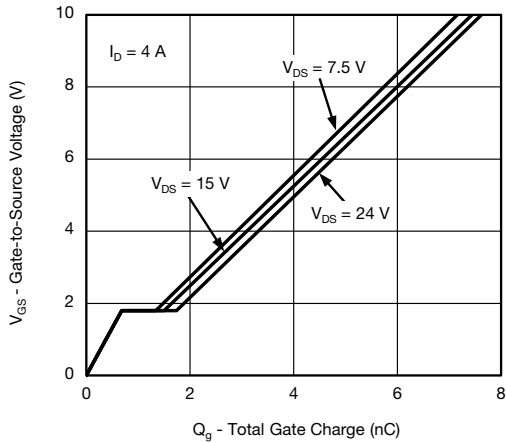


Transconductance

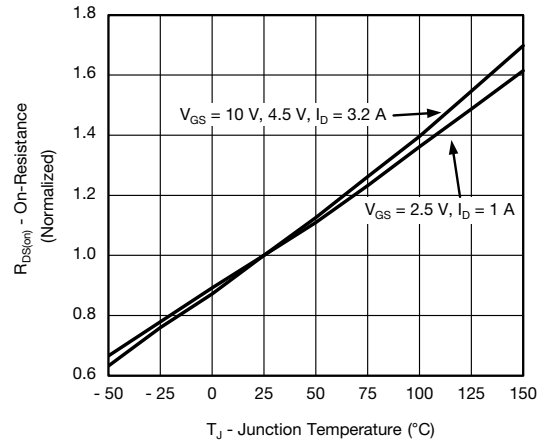


On-Resistance vs. Drain Current

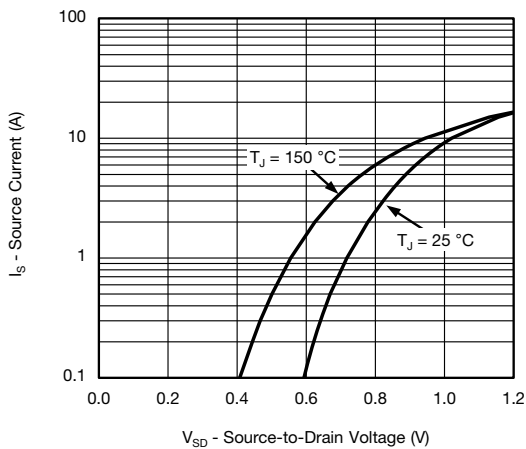
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



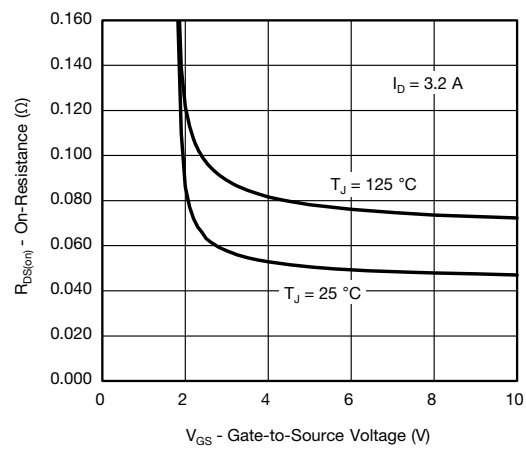
Gate Charge



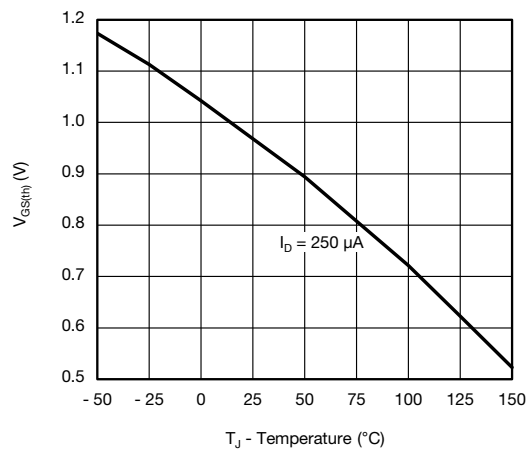
Normalized On-Resistance vs. Junction Temperature



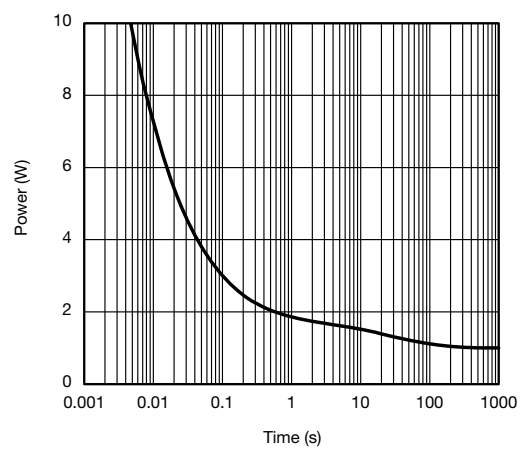
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



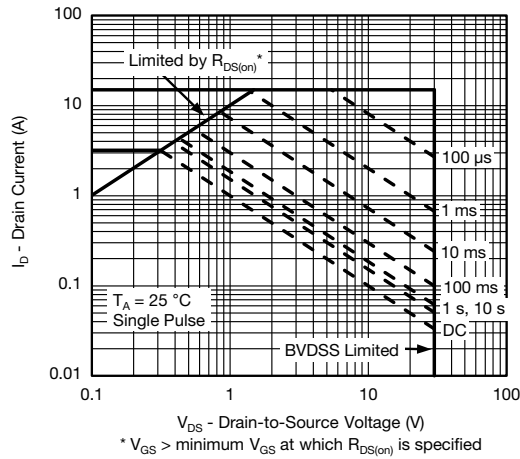
Threshold Voltage



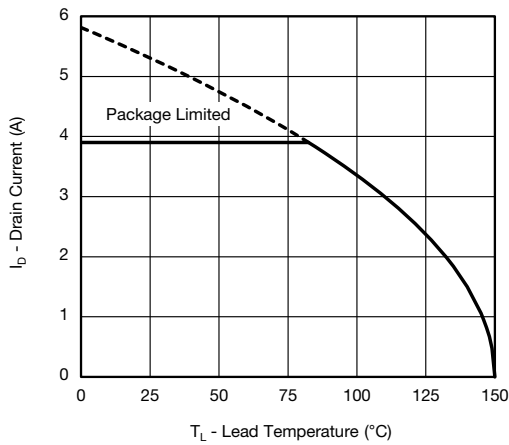
Single Pulse Power, Junction-to-Ambient



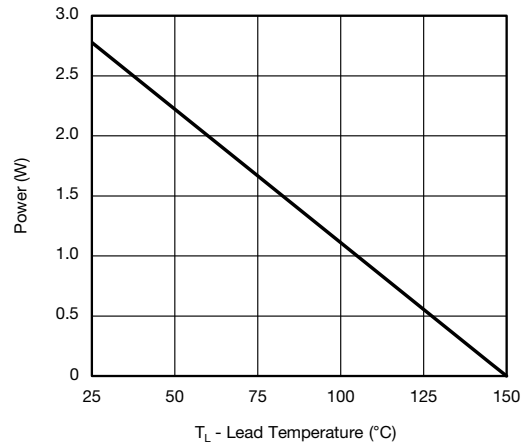
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Safe Operating Area, Junction-to-Ambient



Current Derating^a



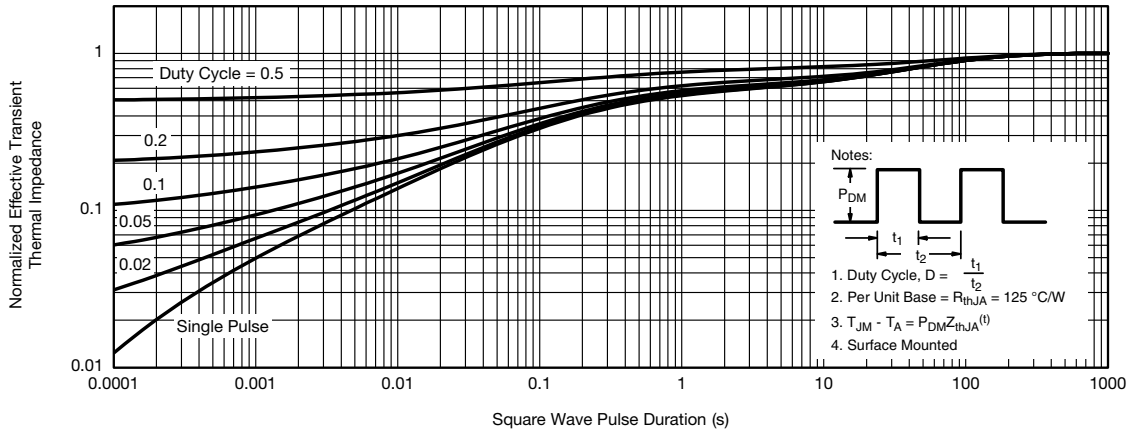
Power Derating

Note

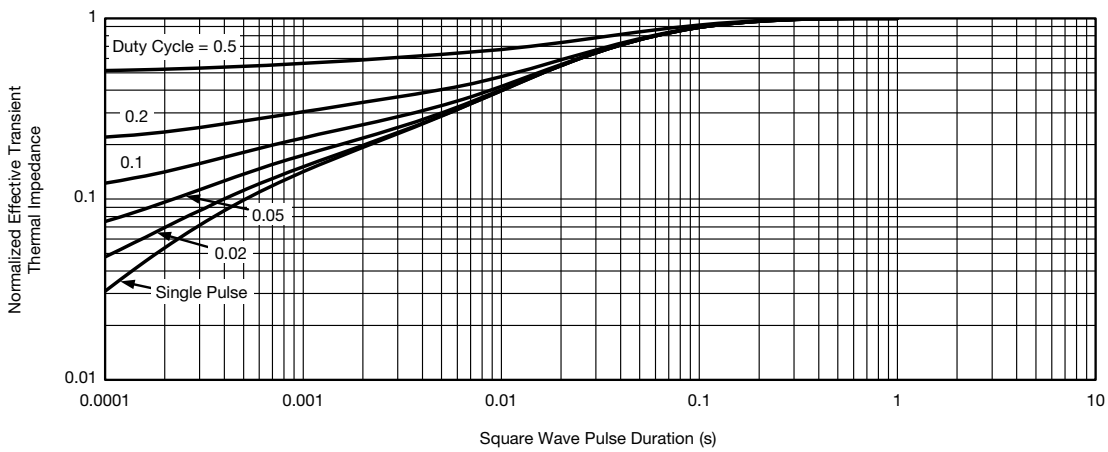
- a. The power dissipation P_D is based on $T_J \text{ max.} = 150\text{ }^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



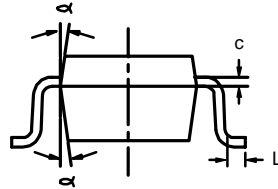
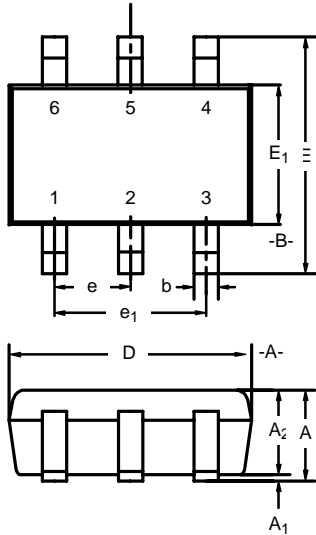
Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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SC-70: 6-LEADS



Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.90	–	1.10	0.035	–	0.043
A ₁	–	–	0.10	–	–	0.004
A ₂	0.80	–	1.00	0.031	–	0.039
b	0.15	–	0.30	0.006	–	0.012
c	0.10	–	0.25	0.004	–	0.010
D	1.80	2.00	2.20	0.071	0.079	0.087
E	1.80	2.10	2.40	0.071	0.083	0.094
E ₁	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65BSC			0.026BSC		
e ₁	1.20	1.30	1.40	0.047	0.051	0.055
L	0.10	0.20	0.30	0.004	0.008	0.012
α	7°Nom			7°Nom		
ECN: S-03946—Rev. B, 09-Jul-01						
DWG: 5550						

Single-Channel LITTLE FOOT® SC-70 6-Pin MOSFET Copper Leadframe Version Recommended Pad Pattern and Thermal Performance

INTRODUCTION

The new single 6-pin SC-70 package with a copper leadframe enables improved on-resistance values and enhanced thermal performance as compared to the existing 3-pin and 6-pin packages with Alloy 42 leadframes. These devices are intended for small to medium load applications where a miniaturized package is required. Devices in this package come in a range of on-resistance values, in n-channel and p-channel versions. This technical note discusses pin-outs, package outlines, pad patterns, evaluation board layout, and thermal performance for the single-channel version.

BASIC PAD PATTERNS

See Application Note 826, *Recommended Minimum Pad Patterns With Outline Drawing Access for Vishay Siliconix MOSFETs*, (<http://www.vishay.com/doc?72286>) for the basic pad layout and dimensions. These pad patterns are sufficient for the low to medium power applications for which this package is intended. Increasing the drain pad pattern yields a reduction in thermal resistance and is a preferred footprint. The availability of four drain leads rather than the traditional single drain lead allows a better thermal path from the package to the PCB and external environment.

PIN-OUT

Figure 1 shows the pin-out description and Pin 1 identification. The pin-out of this device allows the use of four pins as drain leads, which helps to reduce on-resistance and junction-to-ambient thermal resistance.



Top View

FIGURE 1.

For package dimensions see outline drawing SC-70 (6-Leads) (<http://www.vishay.com/doc?71154>)

EVALUATION BOARDS — SINGLE SC70-6

The evaluation board (EVB) measures 0.6 inches by 0.5 inches. The copper pad traces are the same as in Figure 2. The board allows examination from the outer pins to 6-pin DIP connections, permitting test sockets to be used in evaluation testing. See Figure 3.



FIGURE 2. SC-70 (6 leads) Single

The thermal performance of the single 6-pin SC-70 has been measured on the EVB, comparing both the copper and Alloy 42 leadframes. This test was first conducted on the traditional Alloy 42 leadframe and was then repeated using the 1-inch² PCB with dual-side copper coating.



FIGURE 3.

THERMAL PERFORMANCE

Junction-to-Foot Thermal Resistance (Package Performance)

The junction to foot thermal resistance is a useful method of comparing different packages thermal performance.

A helpful way of presenting the thermal performance of the 6-Pin SC-70 copper leadframe device is to compare it to the traditional Alloy 42 version.

Thermal performance for the 6-pin SC-70 measured as junction-to-foot thermal resistance, where the “foot” is the drain lead of the device at the bottom where it meets the PCB. The junction-to-foot thermal resistance is typically 40°C/W in the copper leadframe and 163°C/W in the Alloy 42 leadframe — a four-fold improvement. This improved performance is obtained by the enhanced thermal conductivity of copper over Alloy 42.

Power Dissipation

The typical $R_{\theta JA}$ for the single 6-pin SC-70 with copper leadframe is 103°C/W steady-state, compared with 212°C/W for the Alloy 42 version. The figures are based on the 1-inch² FR4 test board. The following example shows how the thermal resistance impacts power dissipation for the two different leadframes at varying ambient temperatures.

ALLOY 42 LEADFRAME	
Room Ambient 25 °C	Elevated Ambient 60 °C
$P_D = \frac{T_{J(max)} - T_A}{R_{\theta JA}}$	$P_D = \frac{T_{J(max)} - T_A}{R_{\theta JA}}$
$P_D = \frac{150^\circ\text{C} - 25^\circ\text{C}}{212^\circ\text{C}/\text{W}}$	$P_D = \frac{150^\circ\text{C} - 25^\circ\text{C}}{212^\circ\text{C}/\text{W}}$
$P_D = 590 \text{ mW}$	$P_D = 425 \text{ mW}$

COOPER LEADFRAME	
Room Ambient 25 °C	Elevated Ambient 60 °C
$P_D = \frac{T_{J(max)} - T_A}{R_{\theta JA}}$	$P_D = \frac{T_{J(max)} - T_A}{R_{\theta JA}}$
$P_D = \frac{150^\circ\text{C} - 25^\circ\text{C}}{124^\circ\text{C}/\text{W}}$	$P_D = \frac{150^\circ\text{C} - 60^\circ\text{C}}{124^\circ\text{C}/\text{W}}$
$P_D = 1.01 \text{ W}$	$P_D = 726 \text{ mW}$

As can be seen from the calculations above, the compact 6-pin SC-70 copper leadframe LITTLE FOOT power MOSFET can handle up to 1 W under the stated conditions.

Testing

To further aid comparison of copper and Alloy 42 leadframes, Figure 5 illustrates single-channel 6-pin SC-70 thermal performance on two different board sizes and two different pad patterns. The measured steady-state values of $R_{\theta JA}$ for the two leadframes are as follows:

LITTLE FOOT 6-PIN SC-70		
	Alloy 42	Copper
1) Minimum recommended pad pattern on the EVB board V (see Figure 3).	329.7°C/W	208.5°C/W
2) Industry standard 1-inch ² PCB with maximum copper both sides.	211.8°C/W	103.5°C/W

The results indicate that designers can reduce thermal resistance ($R_{\theta JA}$) by 36% simply by using the copper leadframe device rather than the Alloy 42 version. In this example, a 121°C/W reduction was achieved without an increase in board area. If increasing in board size is feasible, a further 105°C/W reduction could be obtained by utilizing a 1-inch² square PCB area.

The copper leadframe versions have the following suffix:

Single: Si14xxEDH
 Dual: Si19xxEDH
 Complementary: Si15xxEDH

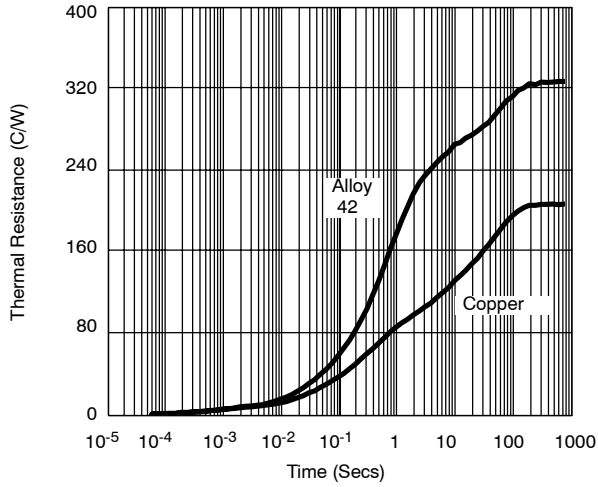


FIGURE 4. Leadframe Comparison on EVB



FIGURE 5. Leadframe Comparison on Alloy 42 1-inch² PCB

RECOMMENDED MINIMUM PADS FOR SC-70: 6-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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